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BT152 series

GENERAL DESCRIPTION

Glass passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

PINNING - TO220AB

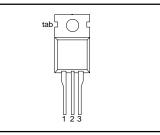
QUICK REFERENCE DATA

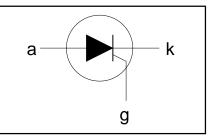
SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} ,	BT152- Repetitive peak off-state	400R 450	600R 650	800R 800	v
V _{RRM} I _{T(AV)}	voltages Average on-state current	13	13	13	A
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	20 200	20 200	20 200	A A

PIN CONFIGURATION

SYMBOL

PIN	DESCRIPTION			
1	cathode			
2	anode			
3	gate			
tab	anode			





LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V _{drm}	Repetitive peak off-state voltages		-	-400R 450 ¹	-600R 650 ¹	-800R 800	V
I _{T(AV)} I _{T(RMS)} I _{TSM}	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 103$ °C all conduction angles half sine wave; $T_j = 25$ °C prior to surge	-		13 20		A A
		t = 10 ms t = 8.3 ms	-		200 220		A A
l ² t	I ² t for fusing	t = 10 ms	-		200		Å ² s
dl _⊤ /dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 50 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu s$	-		200		A/μs
I _{GM}	Peak gate current		-		5		Α
I _{GM} V _{GM}	Peak gate voltage		-		5		V
V _{RGM}	Peak reverse gate voltage		-		5		V
P _{GM}	Peak gate power		-		20		W
P _{G(AV)} T _{stg} T _j	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -		0.5 150 125		°℃ ℃

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance		-	-	1.1	K/W
R _{th j-a}	junction to mounting base Thermal resistance junction to ambient	in free air	-	60	-	K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

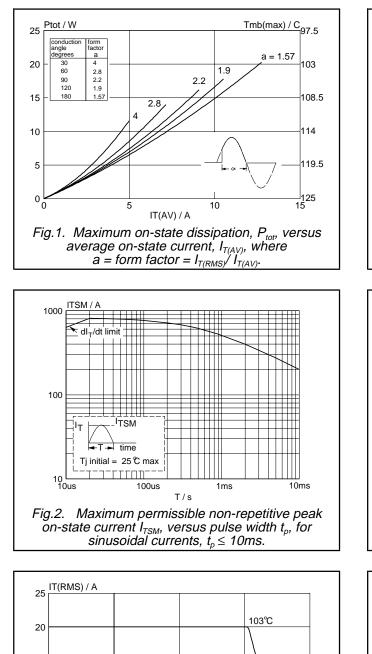
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_{\rm D} = 12 \text{ V}; \text{ I}_{\rm T} = 0.1 \text{ A}$	-	3	32	mA
	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	25	80	mA
	Holding current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	15	60	mA
İ Ϋ _τ	On-state voltage	$I_{T} = 40 \text{ A}$	-	1.4	1.75	V
V _{GT}	Gate trigger voltage	$\dot{V}_{\rm D} = 12 \text{ V}; \text{ I}_{\rm T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_{D} = V_{DRM(max)}$; $I_{T} = 0.1 \text{ A}$; $T_{j} = 125 \text{ °C}$	0.25	0.4	-	V
I _D , I _R	Off-state leakage current	$V_D = V_{DRM(max)}^{ORM(max)}; V_R = V_{RRM(max)}; T_j = 125 \degree C$	-	0.2	1.0	mA

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$ exponential waveform gate open circuit	200	300	-	V/µs
t _{gt}	Gate controlled turn-on	$V_D = V_{DRM(max)}$; $I_G = 0.1$ Å; $dI_G/dt = 5$ Å/µs; $I_{TM} = 40$ Å	-	2	-	μs
t _q	Circuit commutated turn-off time	$V_{D}^{M} = 67\% V_{DRM(max)}; T_{j} = 125 °C;$ $I_{TM} = 50 A; V_{R} = 25 V; dI_{TM}/dt = 30 A/\mu s;$ $dV_{D}/dt = 50 V/\mu s; R_{GK} = 100 \Omega$	-	70	-	μs

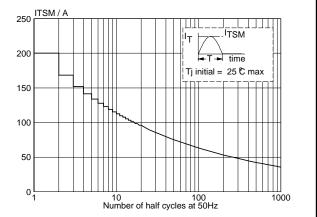
BT152 series

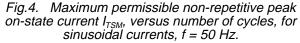


50 Tmb / C

Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

100





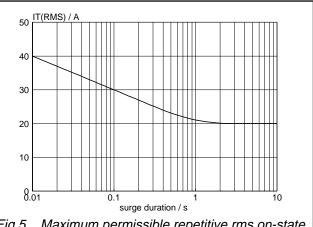
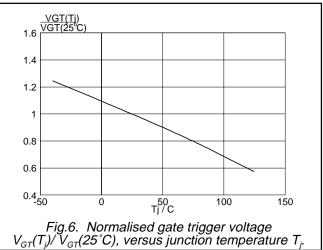


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 103$ °C.



15

10

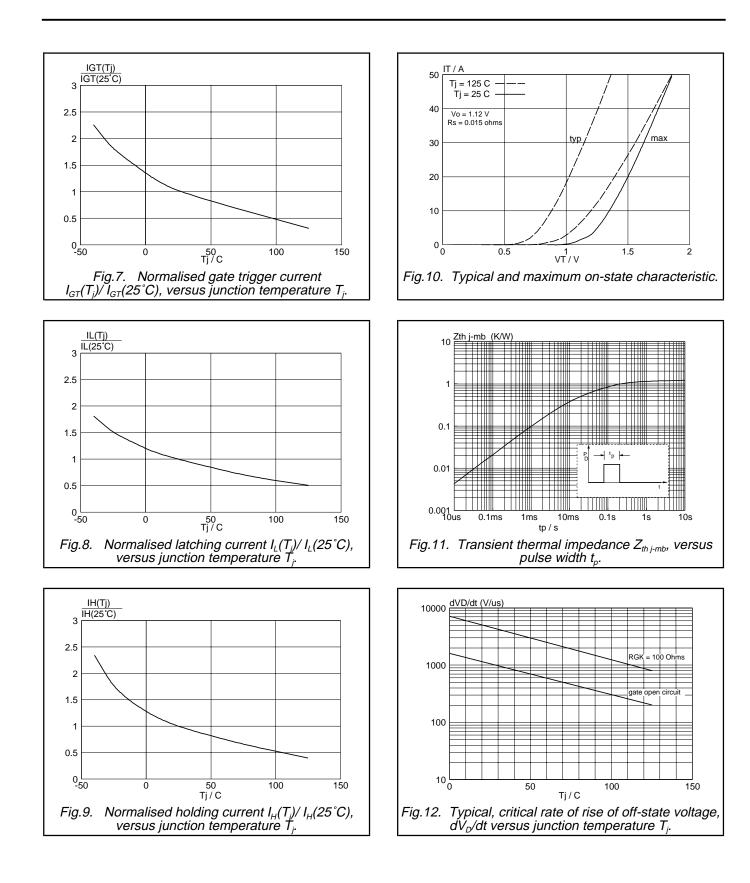
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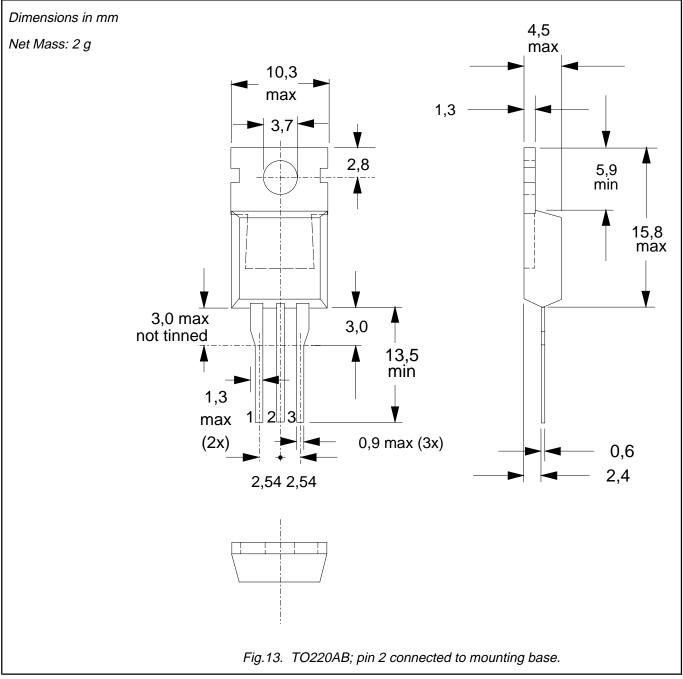
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MECHANICAL DATA



Notes 1. Refer to mounting instructions for TO220 envelopes. 2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status					
Dbjective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification	ification This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
Limiting values					
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.					
Application information					
Where application information is given, it is advisory and does not form part of the specification.					
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